

# BCR8PM-14LD

# Triac

Medium Power Use

REJ03G1565-0100 Rev.1.00 Jul 06, 2007

### **Features**

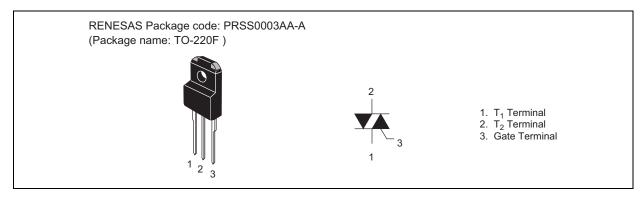
I<sub>T (RMS)</sub>: 8 A
 V<sub>DRM</sub>: 700 V

•  $I_{FGTI}$ ,  $I_{RGTI}$ ,  $I_{RGTIII}$ : 50 mA

• Viso : 2000 V

- The product guaranteed maximum junction temperature 150°C.
- Insulated Type
- Planar Type

### **Outline**



# **Applications**

Motor control, heater control

# **Maximum Ratings**

Parameter	Symbol	Voltage class	Unit	
Faiametei	Symbol	14		
Repetitive peak off-state voltage <sup>Note1</sup>	$V_{DRM}$	700	V	
Non-repetitive peak off-state voltage <sup>Note1</sup>	$V_{DSM}$	800	V	

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I <sub>T (RMS)</sub>	8	А	Commercial frequency, sine full wave 360° conduction, Tc = 85°C
Surge on-state current	I <sub>TSM</sub>	48	А	60Hz sinewave 1 full cycle, peak value, non-repetitive
I <sup>2</sup> t for fusing	l <sup>2</sup> t	9.5	A <sup>2</sup> s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	$P_{GM}$	5	W	
Average gate power dissipation	P <sub>G (AV)</sub>	0.5	W	
Peak gate voltage	$V_{GM}$	10	V	
Peak gate current	I <sub>GM</sub>	2	Α	
Junction temperature	Tj	- 40 to +150	°C	
Storage temperature	Tstg	- 40 to +150	°C	
Mass	_	2.0	g	Typical value
Isolation voltage	Viso	2000	V	Ta = 25°C, AC 1 minute, $T_1 \cdot T_2 \cdot G$ terminal to case

Notes: 1. Gate open.

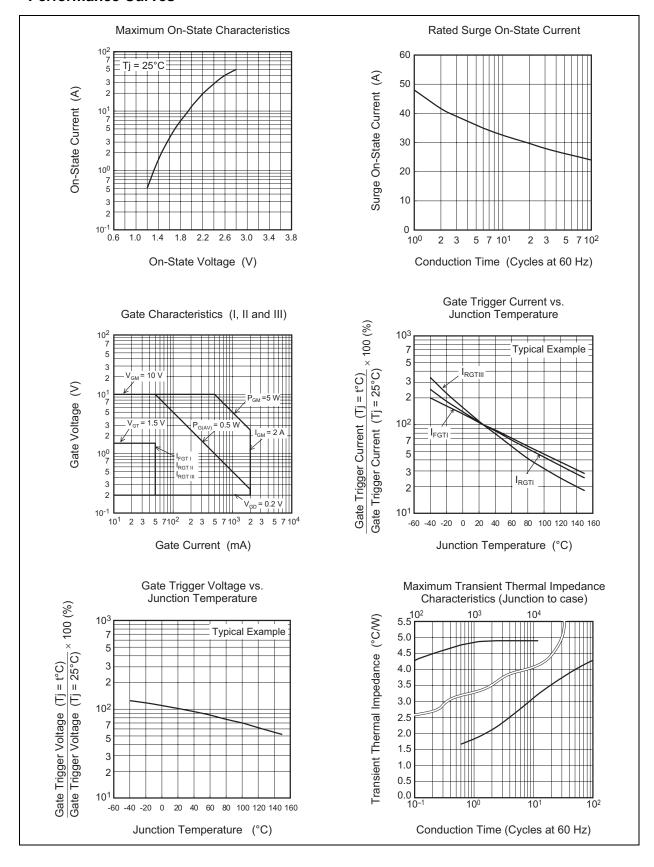
### **Electrical Characteristics**

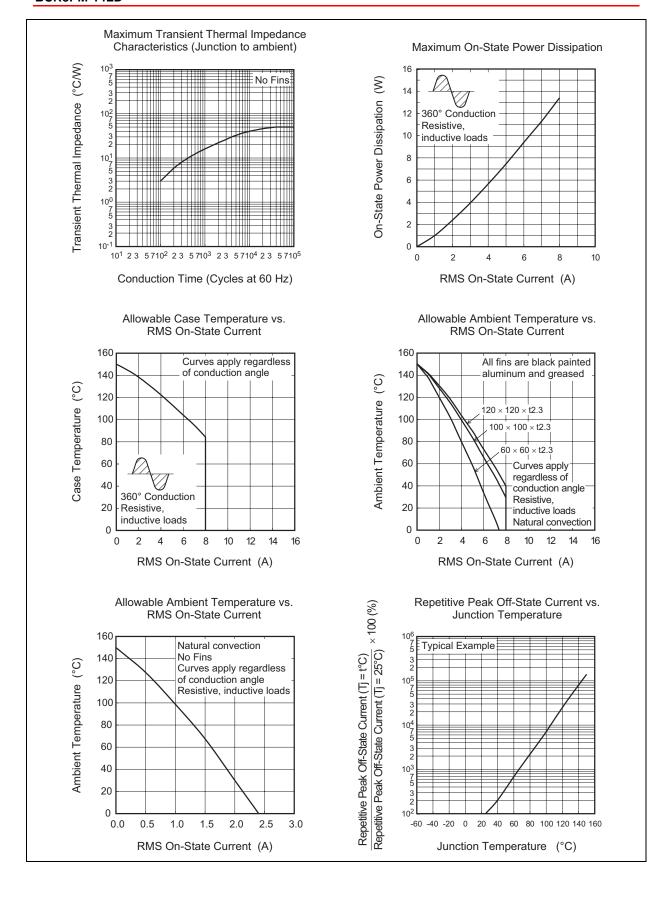
Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state current		I <sub>DRM</sub>	_	_	2.0	mA	Tj = 125°C, V <sub>DRM</sub> applied
On-state voltage		$V_{TM}$	_	_	2.0	V	Tc = 25°C, I <sub>TM</sub> = 12 A, Instantaneous measurement
Gate trigger voltage <sup>Note2</sup>	I	$V_{FGT_I}$	_	_	1.5	V	$Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$
	II	$V_{RGTI}$	_	_	1.5	V	$R_G = 330 \Omega$
	III	$V_{RGTIII}$	_	_	1.5	V	
Gate trigger current <sup>Note2</sup>	I	$I_{FGTI}$	_	_	50	mA	$Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω,
		$I_{RGTI}$	_	_	50	mA	$R_G = 330 \Omega$
	III	$I_{RGTIII}$	1		50	mA	
Gate non-trigger voltage		$V_{GD}$	0.2			>	$Tj = 125^{\circ}C, V_D = 1/2 V_{DRM}$
Thermal resistance		R <sub>th (j-c)</sub>		_	4.9	°C/W	Junction to case <sup>Note3</sup>
Critical-rate of rise of off-state commutating voltage <sup>Note4</sup>		(dv/dt)c	10	ı	ı	V/µs	Tj = 125°C

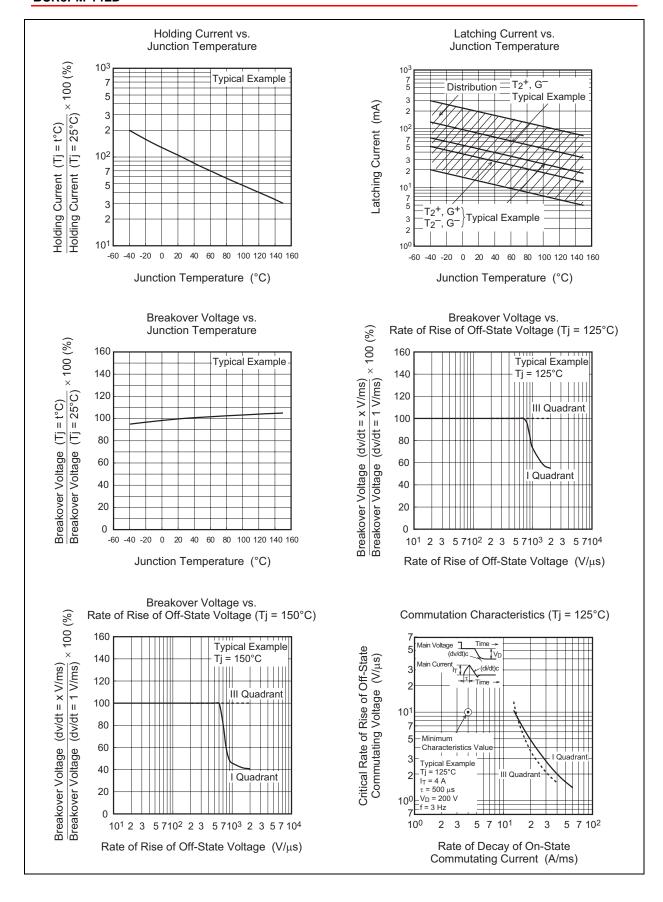
- Notes: 2. Measurement using the gate trigger characteristics measurement circuit.
  - 3. The contact thermal resistance  $R_{th\;(c\text{-}f)}$  in case of greasing is 0.5°C/W.
  - 4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

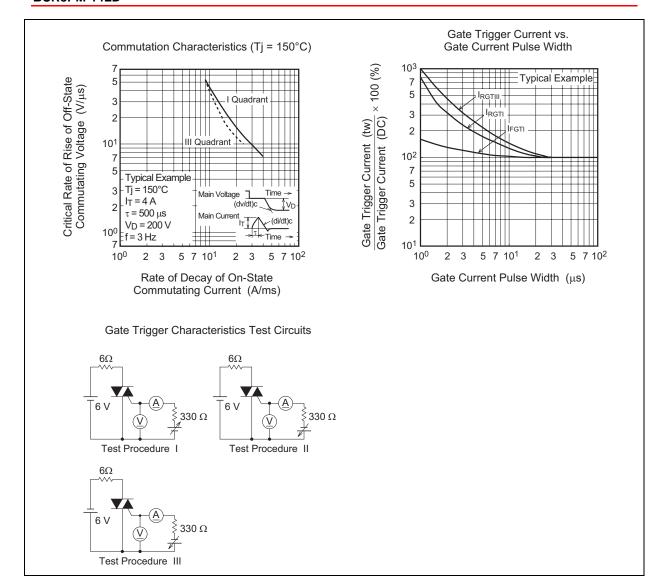
Test conditions	Commutating voltage and current waveforms (inductive load)		
1. Junction temperature  Tj = 125°C	Supply Voltage  →Time		
2. Rate of decay of on-state commutating current (di/dt)c = - 4 A/ms	Main Current (di/dt)c → Time		
3. Peak off-state voltage $V_D = 400 \text{ V}$	Main Voltage Time (dv/dt)c		

### **Performance Curves**

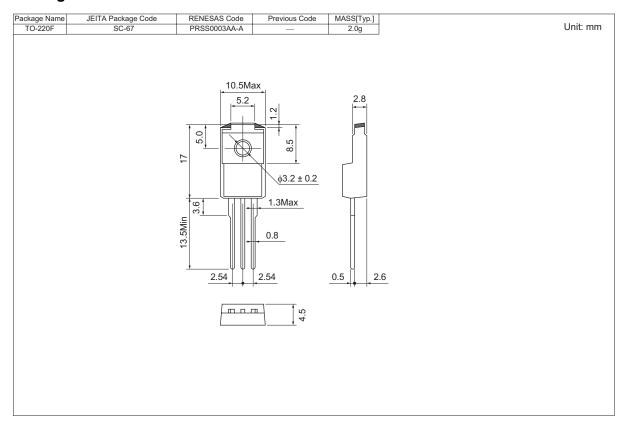








# **Package Dimensions**



# **Order Code**

Lead form	Standard packing	Quantity	Standard order code	Standard order code example	
Straight type	Vinyl sack	100	Type name	BCR8PM-14LD	
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	BCR8PM-14LD-A8	

Note: Please confirm the specification about the shipping in detail.

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